# **Digital Transistors (BRT)** $R1 = 22 k\Omega$ , $R2 = 22 k\Omega$

# **NPN Transistors with Monolithic Bias Resistor Network**

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a baseemitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Base Voltage	$V_{CBO}$	50	Vdc
Collector–Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current – Continuous	IC	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

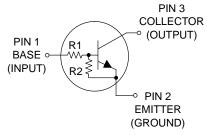
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



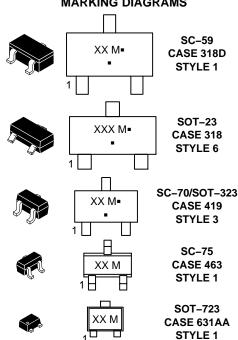
### ON Semiconductor®

#### www.onsemi.com

### PIN CONNECTIONS



#### MARKING DIAGRAMS



= Specific Device Code XXX = Date Code\* M

= Pb-Free Package

X ML<sub>1</sub>

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

SOT-1123

CASE 524AA STYLE 1

**Table 1. ORDERING INFORMATION** 

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2212T1G, NSVMUN2212T1G*	8B	SC-59 (P-Free)	3000 / Tape & Reel
MMUN2212LT1G, NSVMMUN2212LT1G*	A8B	SOT-23 (P-Free)	3000 / Tape & Reel
MUN5212T1G, SMUN5212T1G*	8B	SC-70/SOT-323 (P-Free)	3000 / Tape & Reel
DTC124EET1G, SDTC124EET1G*	8B	SC-75 (P-Free)	3000 / Tape & Reel
DTC124EM3T5G	8B	SOT-723 (P-Free)	8000 / Tape & Reel
NSBC124EF3T5G	L	SOT-1123 (P-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

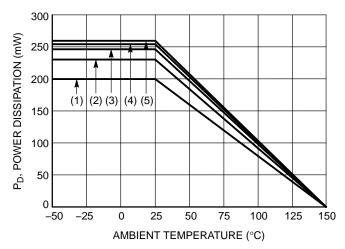


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

**Table 2. THERMAL CHARACTERISTICS** 

	Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTIC	CS (SC-59) (MUN2212)			
Total Device Dissipation $T_A = 25^{\circ}C \qquad \text{(Note 1)} \\ \text{(Note 2)} \\ \text{Derate above } 25^{\circ}C \\ \text{(Note 2)}$	(Note 1)	P <sub>D</sub>	230 338 1.8 2.7	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	540 370	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ hetaJL}$	264 287	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTIC	CS (SOT-23) (MMUN2212L)			
$ \begin{aligned} & \text{Total Device Dissipation} \\ & T_{\text{A}} = 25^{\circ}\text{C} \qquad \text{(Note 1)} \\ & \text{(Note 2)} \\ & \text{Derate above 25}^{\circ}\text{C} \\ & \text{(Note 2)} \end{aligned} $	(Note 1)	P <sub>D</sub>	246 400 2.0 3.2	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	508 311	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ heta JL}$	174 208	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTIC	CS (SC-70/SOT-323) (MUN5212)	Ţ	•	
Total Device Dissipation  T <sub>A</sub> = 25°C (Note 1) (Note 2)  Derate above 25°C (Note 2)	(Note 1)	P <sub>D</sub>	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	618 403	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ heta JL}$	280 332	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTIC	CS (SC-75) (DTC124EE)			
Total Device Dissipation $T_A = 25^{\circ}C \qquad \text{(Note 1)}$ $\text{(Note 2)}$ Derate above 25°C $\text{(Note 2)}$	(Note 1)	P <sub>D</sub>	200 300 1.6 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	600 400	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTIC	CS (SOT-723) (DTC124EM3)	<u>,                                     </u>		
Total Device Dissipation $T_A = 25^{\circ}C \qquad \text{(Note 1)}$ $\text{(Note 2)}$ Derate above 25°C $\text{(Note 2)}$	(Note 1)	P <sub>D</sub>	260 600 2.0 4.8	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	480 205	°C/W
Junction and Storage Temper	ature Range	$T_{J}, T_{stg}$	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.

- FR-4 © Millindin Pad.
   FR-4 © 1.0 x 1.0 Inch Pad.
   FR-4 © 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
   FR-4 © 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 2. THERMAL CHARACTERISTICS** 

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBC124EF3)		-	
Total Device Dissipation  T <sub>A</sub> = 25°C (Note 3)  (Note 4)  Derate above 25°C (Note 3)  (Note 4)	P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, (Note 3) Junction to Ambient (Note 4)	$R_{ heta JA}$	493 421	°C/W
Thermal Resistance, Junction to Lead (Note 3)	R <sub>θ</sub> JL	193	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
   FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

Table 3 FLECTRICAL CHARACTERISTICS (T. - 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Base Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	_	100	nAdc
Collector–Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	_	_	500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	_	0.2	mAdc
Collector–Base Breakdown Voltage ( $I_C = 10 \mu A, I_E = 0$ )	V <sub>(BR)</sub> CBO	50	_	_	Vdc
Collector–Emitter Breakdown Voltage (Note 5) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	50	-	_	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	60	100	_	
Collector–Emitter Saturation Voltage (Note 5) $(I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA})$	V <sub>CE(sat)</sub>	_	-	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ )	V <sub>i(off)</sub>	_	1.2	0.8	Vdc
Input Voltage (on) (V <sub>CE</sub> = 0.3 V, I <sub>C</sub> = 5.0 mA)	V <sub>i(on)</sub>	2.5	1.6	_	Vdc
Output Voltage (on) ( $V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OL</sub>	_	_	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OH</sub>	4.9	-	_	Vdc
Input Resistor	R1	15.4	22	28.6	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

# TYPICAL CHARACTERISTICS MUN2212, MMUN2212L, NSVMMUN2212LT1G, MUN5212, DTC124EE, DTC124EM3

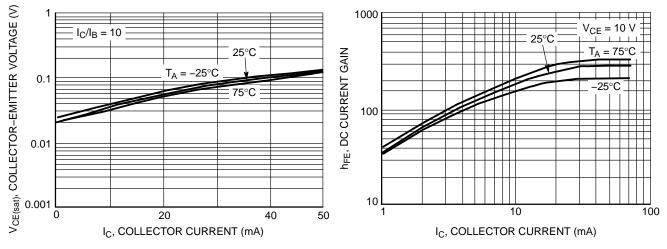


Figure 2. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 3. DC Current Gain

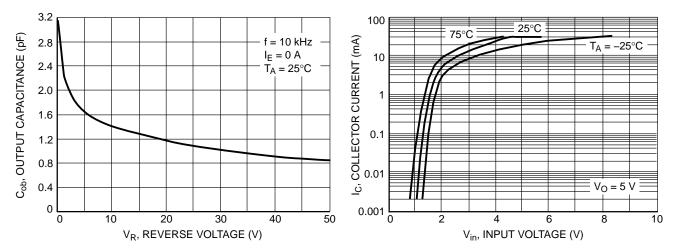


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

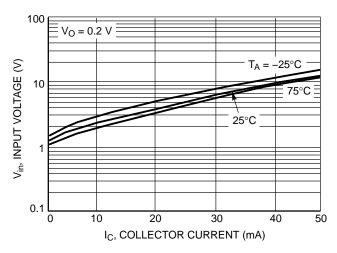


Figure 6. Input Voltage vs. Output Current

## **TYPICAL CHARACTERISTICS - NSBC124EF3**

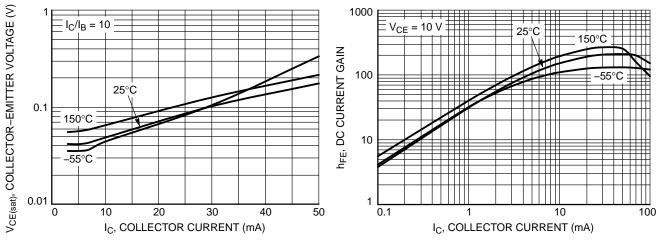


Figure 7. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 8. DC Current Gain

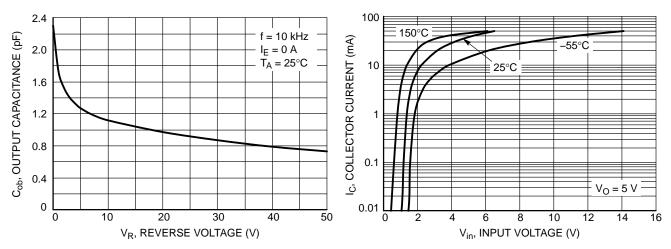


Figure 9. Output Capacitance

Figure 10. Output Current vs. Input Voltage

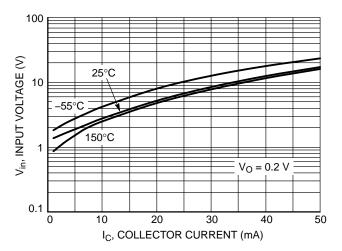


Figure 11. Input Voltage vs. Output Current





SC-70 (SOT-323) **CASE 419** ISSUE R

END VIEW

**DATE 11 OCT 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	M:	ILLIMETE	RS	INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC		0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



## **GENERIC MARKING DIAGRAM**

SIDE VIEW



= Specific Device Code XX

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	<ol><li>CATHODE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1

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## SC75-3 1.60x0.80x0.80, 1.00P **CASE 463 ISSUE H**

**DATE 01 FEB 2024** 

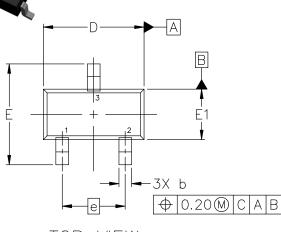
#### NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

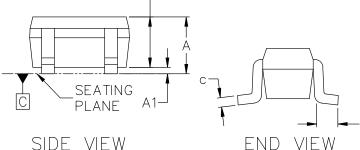
DIM	М	ILLIMETER	RS
DIIVI	MIN.	NOM.	MAX.
А	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	0.80 REF.		
b	0.15	0.20	0.30
С	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
е	1.00 BSC		
L	0.10	0.15	0.20

0.356

0.787



VIEW



A2

SIDE VIEW

## **GENERIC MARKING DIAGRAM\***



XX= Specific Device Code

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. EMITTER

PIN 1. CATHODE 2. CATHODE

3. ANODE

STYLE 4:

STYLE 2: PIN 1. ANODE 2. N/C 3. COLLECTOR 3. CATHODE

STYLE 5:

PIN 1. GATE 2. SOURCE

3. DRAIN

STYLE 3: PIN 1. ANODE 2. ANODE

3. CATHODE

1.000 RECOMMENDED MOUNTING FOOTPRINT\*

1.803

0.508

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Reposite Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SC75-3 1.60x0.80x0.80, 1.0	00P	PAGE 1 OF 1

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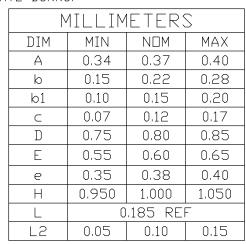


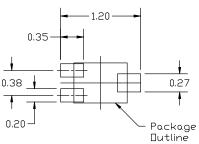
#### SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

**DATE 18 JAN 2024** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
  OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



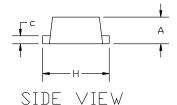


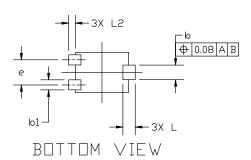
# RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download th e □N Semiconductor Soldering and Mounting Techniques Reference manual, S□L□ERRM/□.

1	-A B T
	E

THP VIFW





# GENERIC MARKING DIAGRAM\*



X = Specific Device Code

M = Date Code

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

YLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
<ol><li>EMITTER</li></ol>	2. N/C	2. ANODE	2. CATHODE	<ol><li>SOURCE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	3. ANODE	3. DRAIN

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P		PAGE 1 OF 1

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MILLIMETERS

 $N\square M$ .

0.50



#### SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

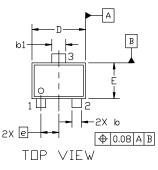
**DATE 24 JAN 2024** 

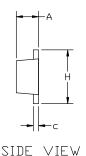
MAX.

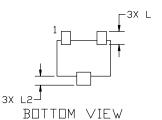
0.55

#### NOTES:

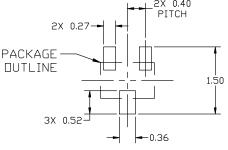
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.







b	0.15	0.21	0.27
b1	0.25	0.31	0.37
С	0.07	0.12	0.17
D	1.15	1.20	1.25
Е	0.75	0.80	0.85
е	0.40 BSC		
Н	1.15	1.20	1.25
L		0.29 REF	-
L2	0.15	0.20	0.25
2X 0.40 PITCH			



DIM

Α

MIN.

0.45

### RECOMMENDED MOUNTING FUUTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
<ol><li>EMITTER</li></ol>	2. N/C	2. ANODE	2. CATHODE	<ol><li>SOURCE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>DRAIN</li></ol>

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